

650V 25A Field Stop Trench IGBT

| V <sub>CES</sub>            | 650V |
|-----------------------------|------|
| I <sub>C(100°C)</sub>       | 25A  |
| V <sub>CE(sat) (Typ.)</sub> | 1.6V |
| P <sub>D</sub>              | 174W |

#### Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Built in Very Fast & Soft Recovery FRD (RFN - Series)
- 5) Pb free Lead Plating ; RoHS Compliant

#### Applications

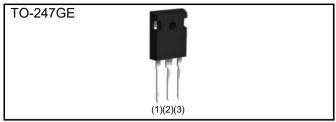
PFC

UPS

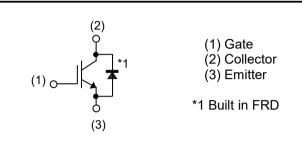
**Power Conditioner** 

IH

#### Outline



#### Inner Circuit



#### Packaging Specifications

|      | Packaging                 | Tube        |
|------|---------------------------|-------------|
|      | Reel Size (mm)            | -           |
| Type | Tape Width (mm)           | -           |
| Туре | Basic Ordering Unit (pcs) | 600         |
|      | Packing code              | C13         |
|      | Marking                   | RGTH50TS65D |

#### •Absolute Maximum Ratings (at T<sub>c</sub> = 25°C unless otherwise specified)

|                                |                                 |                               | ,           |      |
|--------------------------------|---------------------------------|-------------------------------|-------------|------|
| Parameter                      |                                 | Symbol                        | Value       | Unit |
| Collector - Emitter Voltage    |                                 | V <sub>CES</sub>              | 650         | V    |
| Gate - Emitter Voltage         |                                 | V <sub>GES</sub>              | ±30         | V    |
| Collector Current              | $T_{\rm C} = 25^{\circ}{\rm C}$ | ۱ <sub>C</sub>                | 50          | А    |
| Collector Current              | T <sub>C</sub> = 100°C          | ۱ <sub>C</sub>                | 25          | А    |
| Pulsed Collector Current       |                                 | I <sub>CP</sub> *1            | 100         | А    |
| Diode Forward Current          | $T_{\rm C} = 25^{\circ}{\rm C}$ | I <sub>F</sub>                | 35          | А    |
| Diode Forward Current          | T <sub>C</sub> = 100°C          | I <sub>F</sub>                | 20          | А    |
| Diode Pulsed Forward Current   |                                 | I <sub>FP</sub> <sup>*1</sup> | 100         | А    |
| Dower Dissinction              | $T_{C} = 25^{\circ}C$           | P <sub>D</sub>                | 174         | W    |
| Power Dissipation              | T <sub>C</sub> = 100°C          | P <sub>D</sub>                | 87          | W    |
| Operating Junction Temperature |                                 | Tj                            | -40 to +175 | °C   |
| Storage Temperature            |                                 | T <sub>stg</sub>              | -55 to +175 | °C   |
| *1 Dules width limited by T    |                                 |                               |             |      |

\*1 Pulse width limited by T<sub>jmax.</sub>

#### RGTH50TS65DGC13

#### •Thermal Resistance

| Parameter                                | Symbol                   | Values |      |      | Unit |
|--|--------------------------|--------|------|------|------|
|  | Symbol                   | Min.   | Тур. | Max. | Unit |
| Thermal Resistance IGBT Junction - Case  | $R_{\theta(j\text{-}c)}$ | -      | -    | 0.86 | °C/W |
| Thermal Resistance Diode Junction - Case | $R_{\theta(j\text{-}c)}$ | -      | -    | 2.28 | °C/W |

### ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

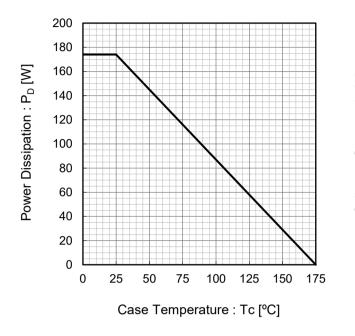
| Parameter                                 | Symbol                 | Conditions   | Values |            |          | Unit |  |
|---|------------------------|--|--------|------------|----------|------|--|
| Faranielei                                | er Symbol Conditions – |  | Min.   | Тур.       | Max.     | Unit |  |
| Collector - Emitter Breakdown<br>Voltage  | BV <sub>CES</sub>      | I <sub>C</sub> = 10μΑ, V <sub>GE</sub> = 0V  | 650    | -          | -        | V    |  |
| Collector Cut - off Current               | I <sub>CES</sub>       | V <sub>CE</sub> = 650V, V <sub>GE</sub> = 0V   | -      | -          | 10       | μA   |  |
| Gate - Emitter Leakage Current            | I <sub>GES</sub>       | V <sub>GE</sub> = ±30V, V <sub>CE</sub> = 0V   | -      | -          | ±200     | nA   |  |
| Gate - Emitter Threshold<br>Voltage       | $V_{GE(th)}$           | V <sub>CE</sub> = 5V, I <sub>C</sub> = 17.5mA  | 4.5    | 5.5        | 6.5      | V    |  |
| Collector - Emitter Saturation<br>Voltage | V <sub>CE(sat)</sub>   | I <sub>C</sub> = 25A, V <sub>GE</sub> = 15V<br>T <sub>j</sub> = 25°C<br>T <sub>j</sub> = 175°C | -      | 1.6<br>2.1 | 2.1<br>- | V    |  |

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

|                                  |                    |   |      | Values  |      |      |
|----------------------------------|--------------------|---|------|---------|------|------|
| Parameter                        | Symbol             | Conditions                                    | Min. | Тур.    | Max. | Unit |
| Input Capacitance                | C <sub>ies</sub>   | V <sub>CE</sub> = 30V                         | -    | 1410    | -    |      |
| Output Capacitance               | C <sub>oes</sub>   | V <sub>GE</sub> = 0V                          | -    | 57      | -    | pF   |
| Reverse Transfer Capacitance     | C <sub>res</sub>   | f = 1MHz                                      | -    | 22      | -    |      |
| Total Gate Charge                | $Q_g$              | V <sub>CE</sub> = 300V                        | -    | 49      | -    |      |
| Gate - Emitter Charge            | $Q_{ge}$           | I <sub>C</sub> = 25A                          | -    | 15      | -    | nC   |
| Gate - Collector Charge          | $Q_{gc}$           | V <sub>GE</sub> = 15V                         | -    | 19      | -    |      |
| Turn - on Delay Time             | t <sub>d(on)</sub> | I <sub>C</sub> = 25A, V <sub>CC</sub> = 400V  | -    | 27      | -    |      |
| Rise Time                        | t <sub>r</sub>     | V <sub>GE</sub> = 15V, R <sub>G</sub> = 10Ω   | -    | 38      | -    | 20   |
| Turn - off Delay Time            | $t_{d(off)}$       | T <sub>j</sub> = 25°C                         | -    | 94      | -    | ns   |
| Fall Time                        | t <sub>f</sub>     | Inductive Load                                | -    | 50      | -    |      |
| Turn - on Delay Time             | t <sub>d(on)</sub> | I <sub>C</sub> = 25A, V <sub>CC</sub> = 400V  | -    | 27      | -    |      |
| Rise Time                        | t <sub>r</sub>     | V <sub>GE</sub> = 15V, R <sub>G</sub> = 10Ω   | -    | 38      | -    | nc   |
| Turn - off Delay Time            | $t_{d(off)}$       | T <sub>j</sub> = 175°C                        | -    | 107     | -    | ns   |
| Fall Time                        | t <sub>f</sub>     | Inductive Load                                | -    | 65      | -    |      |
|                                  |                    | I <sub>C</sub> = 100A, V <sub>CC</sub> = 520V |      |         |      |      |
| Reverse Bias Safe Operating Area | RBSOA              | V <sub>P</sub> = 650V, V <sub>GE</sub> = 15V  | FU   | LL SQUA | RE   | -    |
|                                  |                    | R <sub>G</sub> = 60Ω, T <sub>j</sub> = 175°C  |      |         |      |      |

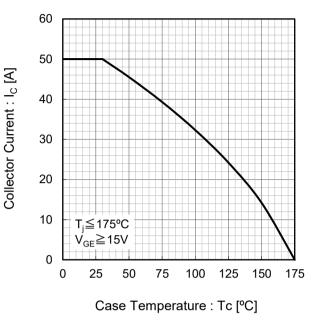
## •FRD Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

| Deremeter                              | Symbol          | Conditions  | Values |              |          | Unit |  |
|--|-----------------|---|--------|--------------|----------|------|--|
| Parameter                              | Symbol          | Conditions  | Min.   | Тур.         | Max.     | Unit |  |
| Diode Forward Voltage                  | V <sub>F</sub>  | I <sub>F</sub> = 20A<br>T <sub>j</sub> = 25°C<br>T <sub>j</sub> = 175°C | -      | 1.45<br>1.25 | 1.9<br>- | v    |  |
| Diode Reverse Recovery Time            | t <sub>rr</sub> | I <sub>F</sub> = 20A  | -      | 58           | -        | ns   |  |
| Diode Peak Reverse Recovery<br>Current | I <sub>rr</sub> | V <sub>CC</sub> = 400V<br>di <sub>F</sub> /dt = 200A/µs                 | -      | 6.3          | -        | А    |  |
| Diode Reverse Recovery<br>Charge       | Q <sub>rr</sub> | T <sub>j</sub> = 25°C   | -      | 0.20         | -        | μC   |  |
| Diode Reverse Recovery Time            | t <sub>rr</sub> | I <sub>F</sub> = 20A  | -      | 256          | -        | ns   |  |
| Diode Peak Reverse Recovery<br>Current | I <sub>rr</sub> | V <sub>CC</sub> = 400V<br>di <sub>F</sub> /dt = 200A/µs                 | -      | 10.4         | -        | А    |  |
| Diode Reverse Recovery<br>Charge       | Q <sub>rr</sub> | T <sub>j</sub> = 175°C  | -      | 1.35         | -        | μC   |  |



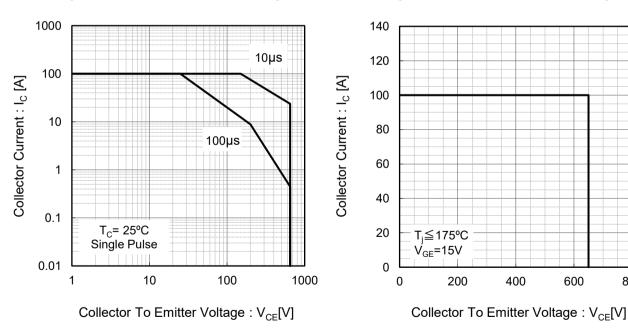
#### Fig.1 Power Dissipation vs. Case Temperature

Fig.2 Collector Current vs. Case Temperature



#### Fig.3 Forward Bias Safe Operating Area

Fig.4 Reverse Bias Safe Operating Area



800

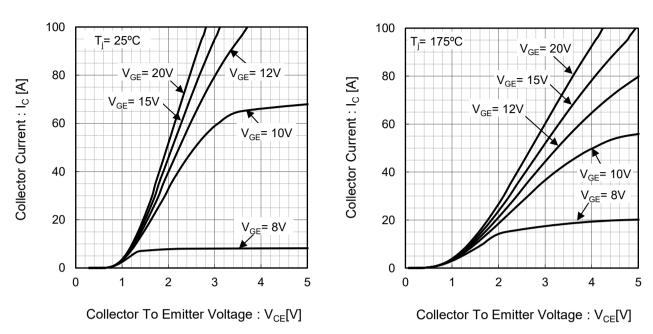


Fig.5 Typical Output Characteristics

Fig.7 Typical Transfer Characteristics

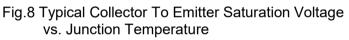
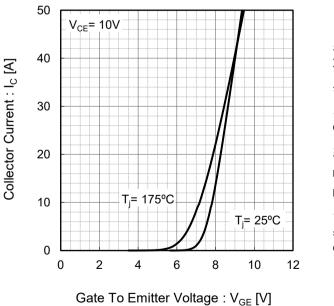


Fig.6 Typical Output Characteristics



4 V<sub>GE</sub>= 15V Collector To Emitter Saturation Voltage I<sub>C</sub>= 50A 3 : V<sub>CE(sat)</sub> [V] I<sub>C</sub>= 25A 2 I<sub>C</sub>= 12A 1 0 25 50 75 100 125 150 175 Junction Temperature : T<sub>i</sub> [°C]

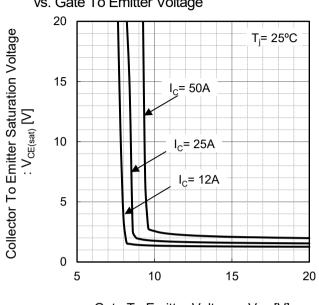
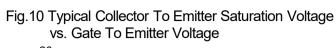
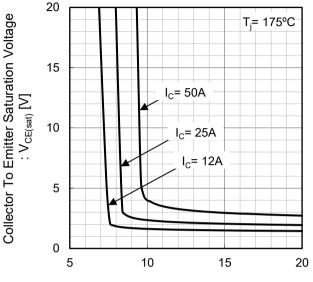


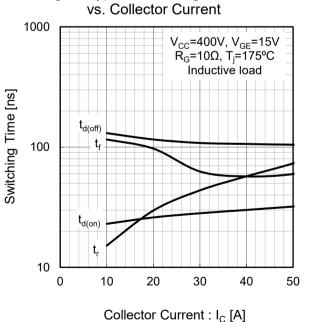
Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

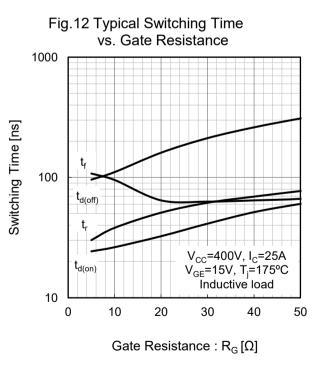




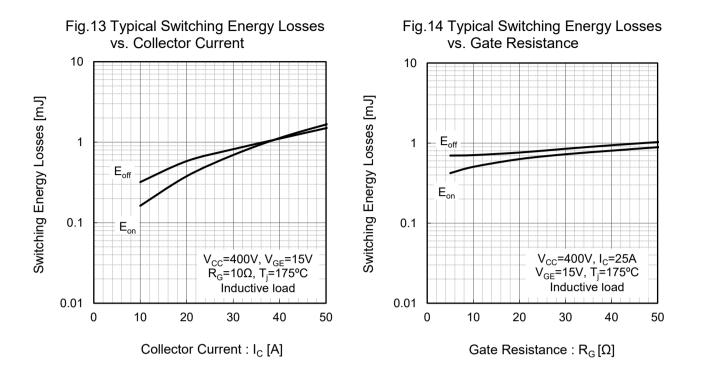
Gate To Emitter Voltage : V<sub>GE</sub> [V]

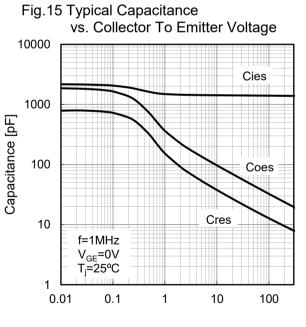
Gate To Emitter Voltage :  $V_{GE}$  [V]





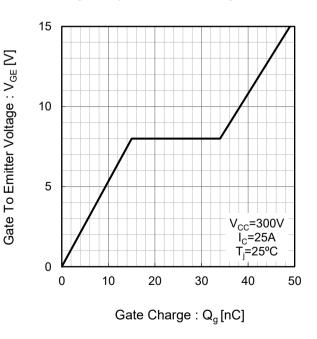
# Fig.11 Typical Switching Time

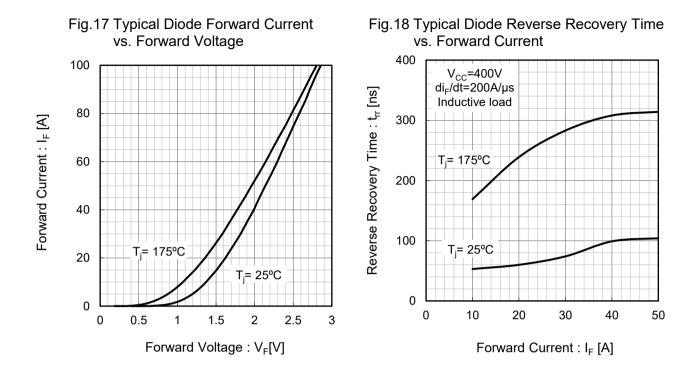




Collector To Emitter Voltage :  $V_{CE}[V]$ 

Fig.16 Typical Gate Charge





## Fig.19 Typical Diode Reverse Recovery Current vs. Forward Current

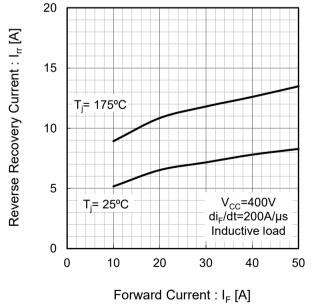
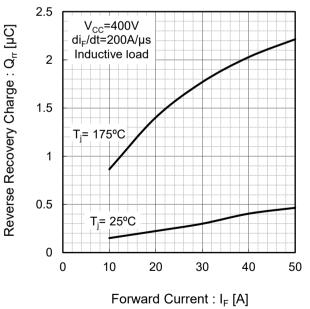


Fig.20 Typical Diode Reverse Recovery Charge vs. Forward Current



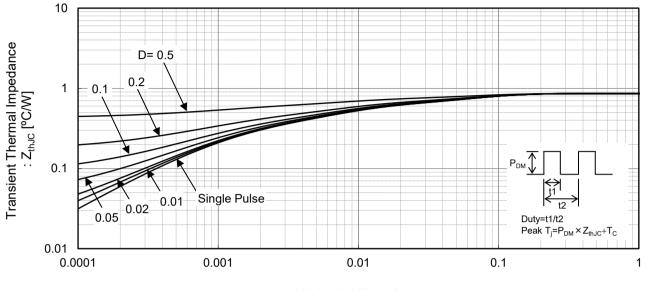
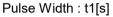


Fig.21 IGBT Transient Thermal Impedance



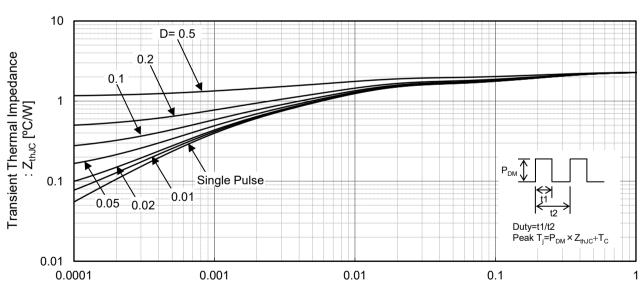


Fig.22 Diode Transient Thermal Impedance

Pulse Width : t1[s]

#### ●Inductive Load Switching Circuit and Waveform

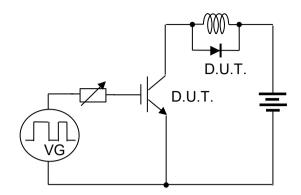


Fig.23 Inductive Load Circuit

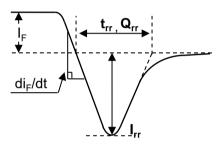


Fig.25 Diode Reverce Recovery Waveform

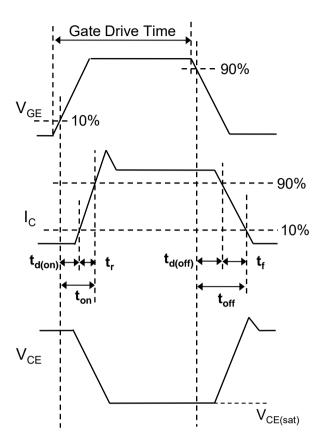


Fig.24 Inductive Load Waveform



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|-----|--|
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